

04/11/2012

Form PTO-1595 (Rev. 03-11)
OMB No. 0651-0027 (exp. 03/31/2012)



U.S. DEPARTMENT OF COMMERCE
United States Patent and Trademark Office

103643246

PATENTS ONLY

2-28-12

To the Director of the U.S. Patent and Trademark Office: Please record the attached documents or the new address(es) below.

1. Name of conveying party(ies)

S.O.I. TEC SILICON ON INSULATOR TECHNOLOGIES
Chemin des Franques
Parc Technologique des Fontaines
Bernin, France 38190

Additional name(s) of conveying party(ies) attached? Yes No

2. Name and address of receiving party(ies)

Name: Soitec

Internal Address: _____

Street Address: Chemin des Franques

Parc Technologique des Fontaines

City: Bemin

State: _____

Country: France Zip: 38190

Additional name(s) & address(es) attached? Yes No

3. Nature of conveyance/Execution Date(s):

Execution Date(s) September 6, 2011

- Assignment Merger
- Security Agreement Change of Name
- Joint Research Agreement
- Government Interest Assignment
- Executive Order 9424, Confirmatory License
- Other _____

4. Application or patent number(s):

This document is being filed together with a new application.

A. Patent Application No.(s)

B. Patent No.(s)

See attached Schedule A

Additional numbers attached? Yes No

5. Name and address to whom correspondence concerning document should be mailed:

Name: TraskBritt

Internal Address: _____

Street Address: P.O. Box 2550

City: Salt Lake City

State: UT Zip: 84110-2550

Phone Number: 801-532-1922

Fax Number: 801-531-9168

Email Address: usptomail@traskbritt.com

6. Total number of applications and patents involved: 52

7. Total fee (37 CFR 1.21(h) & 3.41) \$2080.00

- Authorized to be charged to deposit account
- Enclosed
- None required (government interest not affecting title)

8. Payment Information

Deposit Account Number 201469
04/19/2012 HTON11 00000015 201469 123 0345
Authorized User Name TraskBritt
01 FC:8021 2000.00 DA

9. Signature:

Signature

February 28, 2012

Date

J. Jeffrey Gunn; Reg. No. 56,957
Name of Person Signing

Total number of pages including cover sheet, attachments, and documents:

13

Documents to be recorded (including cover sheet) should be faxed to (571) 273-0140, or mailed to:
Mail Stop Assignment Recordation Services, Director of the USPTO, P.O. Box 1450, Alexandria, V.A. 22313-1450

Attorney Docket No. 3356-001 (E11/0904 EHU)

Schedule A

	Application No.	Filing Date	Country	Attorney Docket No.	Title
1	12/310,345	2/20/2009	US	9373US (G04/0907BF EMT)	PROCESS FOR MAKING A GAN SUBSTRATE
2	12/463,873	5/11/2009	US	9451US (F07/0908BFA)	RELAXATION AND TRANSFER OF STRAINED LAYERS
3	12/450,295	9/18/2009	US	9629US (F06/0907 CF EBI)	A (110) ORIENTED SILICON SUBSTRATE AND A BONDED PAIR OF SUBSTRATES COMPRISING SAID (110) ORIENTED SILICON SUBSTRATE
4	12/563,327	9/21/2009	US	9200.1US (F07/1102CA)	METHODS AND STRUCTURES FOR ALTERING STRAIN IN III-NITRIDE MATERIALS
5	12/576,116	10/8/2009	US	8994.1US (F07/1101CA GLA)	METHODS OF FORMING LAYERS OF SEMICONDUCTOR MATERIAL HAVING REDUCED LATTICE STRAIN, SEMICONDUCTOR STRUCTURES, DEVICES AND ENGINEERED SUBSTRATES INCLUDING SAME
6	12/610,065	10/30/2009	US	8973.1US (F07/0902FL GLA)	STRAIN ENGINEERED COMPOSITE SEMICONDUCTOR SUBSTRATES AND METHODS OF FORMING SAME
7	12/610,092	10/30/2009	US	9358.1US (F08/1104CA GLA)	EPITAXIAL METHODS AND STRUCTURES FOR FORMING SEMICONDUCTOR MATERIALS
8	12/312,017	11/24/2009	US	9397US (F06/0604EN EBI)	IMPROVED PROCESS FOR TRANSFER OF A THIN LAYER FORMED IN A SUBSTRATE WITH VACANCY CLUSTERS

	Application No.	Filing Date	Country	Attorney Docket No.	Title
9	12/663,254	12/4/2009	US	9792US (F07/0110CAU EBI)	METHOD FOR RECYCLING A SUBSTRATE, LAMINATED WATER FABRICATING METHOD AND SUITABLE RECYCLED DONOR SUBSTRATE
10	12/598,403	2/25/2010	US	9703US (F06/1113KR EBI)	IMPROVED PROCESS FOR PREPARING CLEANED SURFACES OF STRAINED SILICON
11	12/712,938	2/25/2010	US	9928US (F08/1004SK EBI)	METHOD FOR TRANSFERRING A LAYER FROM A DONOR SUBSTRATE ONTO A HANDLE SUBSTRATE
12	12/726,800	3/18/2010	US	9944US (F08/0916BYN EBI)	HYBRID SEMICONDUCTOR SUBSTRATE INCLUDING SEMICONDUCTOR-ON-INSULATOR REGION AND METHOD OF MAKING THE SAME (As Amended)
13	12/742,424	5/11/2010	US	P10043US (F06/0806FA ALD)	PROCESS FOR MANUFACTURING A COMPOSITE SUBSTRATE
14	12/678,978	5/28/2010	US	9931US (F07/0502CA GLA)	SEMICONDUCTOR STRUCTURE HAVING A PROTECTIVE LAYER
15	12/814,936	6/14/2010	US	P10054US (F09/0204RB GLA)	SYSTEMS AND METHODS FOR A GAS TREATMENT OF A NUMBER OF SUBSTRATES
16	12/808,353	6/15/2010	US	P10041US (F06/1204AAB GLA)	METHOD FOR TREATING GERMANIUM SURFACES AND SOLUTIONS TO BE EMPLOYED THEREIN
17	12/820,326	6/22/2010	US	9588.1US (F09/0505CA GLA)	METHODS AND STRUCTURES FOR BONDING ELEMENTS

	Application No.	Filing Date	Country	Attorney Docket No.	Title
18	12/811,203	6/29/2010	US	P10034US (F07/0622CLN ALD)	PROCESS OF TREATING DEFECTS DURING THE BONDING OF WAFERS
19	12/837,326	7/15/2010	US	9975US (F10/0314 MSA GLA)	METHODS OF FORMING BONDED SEMICONDUCTOR STRUCTURES, AND SEMICONDUCTOR STRUCTURES FORMED BY SUCH METHODS
20	12/839,203	7/19/2010	US	9978US (F10/0313 MSA GLA)	TEMPORARY SEMICONDUCTOR STRUCTURE BONDING METHODS AND RELATED BONDED SEMICONDUCTOR STRUCTURES
21	12/865,838	8/2/2010	US	P10106US (F07/0509MSH ALD)	SUBSTRATE HAVING A CHARGED ZONE IN AN INSULATING BURIED LAYER
22	12/851,227	8/5/2010	US	P10123US (F07/0624CLN ALD)	PROCESS FOR BONDING AND TRANSFERRING A LAYER
23	12/879,637	9/10/2010	US	P10141US (F10/0502MSA GLA)	METHODS OF FORMING THROUGH WAFER INTERCONNECTS IN SEMICONDUCTOR STRUCTURES USING SACRIFICIAL MATERIAL, AND SEMICONDUCTOR STRUCTURES FORMED BY SUCH METHODS
24	12/890,220	9/24/2010	US	9583.2US (F09/0603 FLE)	METHODS OF FABRICATING SEMICONDUCTOR STRUCTURES AND DEVICES USING GLASS BONDING LAYERS, AND SEMICONDUCTOR STRUCTURES AND DEVICES FORMED BY SUCH METHODS

	Application No.	Filing Date	Country	Attorney Docket No.	Title
25	12/894,724	9/30/2010	US	P10058US (F100307RB GLA)	THERMALIZING GAS INJECTORS FOR GENERATING INCREASED PRECURSOR GAS, MATERIAL DEPOSITION SYSTEMS INCLUDING SUCH INJECTORS, AND RELATED METHODS
26	12/895,311	9/30/2010	US	P10096US (F10/0312CW GLA)	SYSTEMS AND METHODS FOR FORMING SEMICONDUCTOR MATERIALS BY ATOMIC LAYER DEPOSITION
27	12/935,857	9/30/2010	US	P10187US (F07/1106CA GLA)	FORMATION OF SUBSTANTIALLY PIT FREE INDIUM GALLIUM NITRIDE
28	12/936,639	11/15/2010	US	P10190US (F08/0613ACS ALD)	A METHOD OF INITIATING MOLECULAR BONDING
29	12/970,422	12/16/2010	US	P10171US (F10/0806MSA GLA)	METHODS FOR DIRECTLY BONDING TOGETHER SEMICONDUCTOR STRUCTURES, AND BONDED SEMICONDUCTOR STRUCTURES FORMED USING SUCH METHODS
30	12/977,999	12/23/2010	US	P10142US (F10/0419CW GLA)	STRAIN RELAXATION USING METAL MATERIALS AND RELATED STRUCTURES
31	13/020,288	2/3/2011	US	P10188US (F10/0901CW GLA)	METALLIC CARRIER FOR LAYER TRANSFER AND METHODS FOR FORMING THE SAME
32	13/029,213	2/17/2011	US	P10143US (F10/0503CFG GLA)	III-V SEMICONDUCTOR STRUCTURES WITH DIMINISHED PIT DEFECTS AND METHODS FOR FORMING THE SAME

	Application No.	Filing Date	Country	Attorney Docket No.	Title
33	13/060,398	2/23/2011	US	8900.1US (F08/0113CA GLA)	METHODS OF FABRICATING SEMICONDUCTOR STRUCTURES OR DEVICES USING LAYERS OF SEMICONDUCTOR MATERIAL HAVING SELECTED OR CONTROLLED LATTICE PARAMETERS
34	13/038,920	3/2/2011	US	P10345US (F10/0706CFG GLA)	METHODS OF FORMING III/V SEMICONDUCTOR MATERIALS, AND SEMICONDUCTOR STRUCTURES FORMED USING SUCH METHODS
35	13/043,088	3/8/2011	US	P10297US (F09/1010AV ALD)	PROCESS FOR FABRICATING A MULTILAYER STRUCTURE WITH POST-GRINDING TRIMMING
36	13/069,900	3/23/2011	US	9973.1US (F09/0902EL GLA)	III-V SEMICONDUCTOR STRUCTURES AND METHODS FOR FORMING THE SAME
37	13/077,292	3/31/2011	US	9979US (F10/0306 MSA GLA)	METHODS OF FORMING BONDED SEMICONDUCTOR STRUCTURES, AND SEMICONDUCTOR STRUCTURES FORMED BY SUCH METHODS
38	13/077,364	3/31/2011	US	P10010US (F10/0420MSA GLA)	METHODS OF FORMING BONDED SEMICONDUCTOR STRUCTURES INCLUDING TWO OR MORE PROCESSED SEMICONDUCTOR STRUCTURES CARRIED BY A COMMON SUBSTRATE, AND SEMICONDUCTOR STRUCTURES FORMED BY SUCH METHODS

	Application No.	Filing Date	Country	Attorney Docket No.	Title
39	13/076,745	3/31/2011	US	P10247US (F10/0902MSA GLA)	METHODS FOR BONDING SEMICONDUCTOR STRUCTURES INVOLVING ANNEALING PROCESSES, AND BONDED SEMICONDUCTOR STRUCTURES AND INTERMEDIATE STRUCTURES FORMED USING SUCH METHODS
40	12/937,920	4/5/2011	US	P10222US (F08/0507ND ALD)	PROCESS FOR MANUFACTURING A STRUCTURE COMPRISING A GERMANIUM LAYER ON A SUBSTRATE
41	13/123,180	4/7/2011	US	P10531US (F08/0608GWG ALD)	A METHOD OF PRODUCING A SILICON-ON-SAPPHIRE TYPE HETEROSTRUCTURE
42	13/126,376	4/27/2011	US	P10518US (F08/0717OK ALD)	METHOD TO FABRICATE AND TREAT A STRUCTURE OF SEMICONDUCTOR-ON-INSULATOR TYPE, ENABLING... DISPLACEMENT OF DISLOCATIONS, AND CORRESPONDING STRUCTURE
43	13/133,118	6/8/2011	US	P10599US (F08/0115CLN ALD)	METHODS FOR TESTING SEMICONDUCTOR-ON-INSULATOR TYPE SUBSTRATES, AND SEMICONDUCTOR-ON-INSULATOR SUBSTRATES CONFIGURED FOR TESTING THEREOF
44	13/143,038	6/30/2011	US	P10639US (F08/0901DLN ALD)	A METHOD OF PRODUCING A LAYER OF CAVITIES
45	13/143,170	7/1/2011	US	P10658US (F08/0912GR ALD)	METHOD FOR MANUFACTURING COMPONENTS
46	13/185,044	7/18/2011	US	P10277US (F09/0406MSA GLA)	BONDING SURFACES FOR DIRECT BONDING OF SEMICONDUCTOR STRUCTURES
47	13/147,749	8/3/2011	US	P10682US (F08/0914PGU EMT)	ADAPTATION OF THE LATTICE PARAMETER OF A LAYER OF STRAINED

	Application No.	Filing Date	Country	Attorney Docket No.	Title
					MATERIAL
48	13/206,242	8/9/2011	US	P10284US (F10/1107BYN GLA)	METHODS OF FORMING BONDED SEMICONDUCTOR STRUCTURES INCLUDING INTERCONNECT-LAYERS HAVING ONE OR MORE OF ELECTRICAL, OPTICAL, AND FLUIDIC INTERCONNECTS THEREIN, AND BONDED SEMICONDUCTOR STRUCTURES FORMED USING SUCH METHODS
49	13/206,280	8/9/2011	US	P10285US (F10/1106MSA GLA)	METHODS OF FORMING BONDED SEMICONDUCTOR STRUCTURES IN 3D INTEGRATION PROCESSES USING RECOVERABLE SUBSTRATES, AND BONDED SEMICONDUCTOR STRUCTURES FORMED BY SUCH METHODS
50	13/206,299	8/9/2011	US	P10424US (F10/1203BYN GLA)	THREE DIMENSIONALLY INTEGRATED SEMICONDUCTOR SYSTEMS INCLUDING PHOTOACTIVE DEVICES AND SEMICONDUCTOR-ON-INSULATOR SUBSTRATES, AND METHODS OF FORMING SUCH THREE DIMENSIONALLY INTEGRATED SEMICONDUCTOR SYSTEMS
51	13/201,365	8/12/2011	US	P10662US (F08/0724FLE EMT)	RELAXATION AND TRANSFER OF STRAINED MATERIAL LAYERS
52	13/255,670	10/18/2011	US	P10683US (F07/0801MRK ALD)	METHOD OF FABRICATING A MULTILAYER STRUCTURE WITH CIRCUIT LAYER TRANSFER

Extrait du registre du commerce et des sociétés

IMMATRICULATION ET IDENTITE DE LA PERSONNE

Numéro d'immatriculation : 384 711 909 RCS Grenoble
 Date d'immatriculation : 11 mars 1992
 Dénomination : Sottec
 Forme juridique : Société anonyme à conseil d'administration
 Durée de la personne morale : 80 années

CARACTERISTIQUES DE L'ENTREPRISE

Capital : 12 210 573,20 EUROS
 Siège social : Parc Technologique des Fontaines chemin Des Franques 38190 Beron - FRANCE
 Activités principales de l'entreprise : Mise au point, recherche et fabrication comme réalisation de matériaux pour la micro-électronique et pour l'industrie générale, technologies diverses, développement de machines spécifiques et implémentations logicielles pour les besoins particuliers de l'industrie et des laboratoires de recherche et développement.

Date de clôture de l'exercice :

Président du conseil d'administration :

Monsieur ALBERTON HERVE André (e) né le 02 novembre 1941 à RAFFAY - Maroc - de nationalité française

Directeur général :

Monsieur ALBERTON HERVE André (e) né le 02 novembre 1941 à RAFFAY - Maroc - de nationalité française
 Nom d'usage : Monsieur ALBERTON HERVE André
 domicile : 127e chemin de Jallières 38240 MEVIAN - FRANCE

Directeur général délégué :

Monsieur ALBERTON HERVE André (e) né le 02 novembre 1941 à RAFFAY - Maroc - de nationalité française

Nom d'usage : Monsieur ALBERTON HERVE André
 domicile : 127e chemin de Jallières 38240 MEVIAN - FRANCE

Administrateur :

Monsieur BOUDRE Paul Antoine né le 14 novembre 1959 à TULLE (19) - France - de nationalité française

Nom d'usage : Monsieur BOUDRE Paul
 domicile : 192 rue de la gare 19041 TULLE - FRANCE

Administrateur :

Monsieur HIROSE Junia né le 01 juillet 1947 à SAPPORO - Japon - de nationalité japonaise

Nom d'usage : Monsieur HIROSE Junia
 domicile : 23 rue du Parc Deschamps Wingmann West Lothian ah 54 8 88 - ROYAUME UNI

Administrateur :

Monsieur MARTIN Joseph Robert né le 09 décembre 1947 à PENNSYLVANIA - Etats Unis d'Amérique - de nationalité américaine

Nom d'usage : Monsieur MARTIN Joseph
 domicile : 17 Sarnoway Road ME04110 Cumberland Foreside - ETATS UNIS D'AMERIQUE

Madame GRANBLEMENT Annie Denise née le 24 mai 1936 à PARIS 16e arrdt 75 - France - de nationalité française

Nom d'usage : Madame PASCAL Annie
 domicile : 19 avenue Terre 73210 Saint-gratien - FRANCE

administrateur

Monsieur MURRAY Patrick Foy né(e) le 12 décembre 1944 à MICHIGAN - Etats-Unis d'Amérique - de nationalité américaine
 Nom d'usage : Monsieur MURRAY Patrick
 domicile : 40 avenue de Saxe 75007 Paris - FRANCE

administrateur

Monsieur DUNN Douglas John né(e) le 05 mai 1944 à ROTHERHAM - Pays-Bas - de nationalité néerlandaise
 Nom d'usage : Monsieur DUNN Douglas
 domicile : Millstone House Mill Lane Swindon au 1-4ng - ROYAUME-UNI

administrateur

Monsieur LAMOUCHE Didier René né(e) le 07 mai 1953 à MELKES - Maroc - de nationalité française
 Nom d'usage : Monsieur LAMOUCHE Didier
 domicile : 6 rue du Général Pershing 78000 Versailles - FRANCE

commissaire aux comptes titulaire

CABINET MURAZ PAVILLET Société à responsabilité limitée - 347 333 690 RCS Grenoble
 siège social : 3 chemin du Vieux Chêne 38240 Meylan - FRANCE

commissaire aux comptes titulaire

TRIGEWATERHOUSECOOPERS AUDIT - 672 006 483 RCS Nanterre
 siège social : 63 rue de Villiers 92208 Neuilly Sur Seine - FRANCE

commissaire aux comptes suppléant

Monsieur PERROT René Charles né(e) le 22 juin 1948 à PONT DE BEAUVOISIN (38) - France - de nationalité française
 Nom d'usage : Monsieur PERROT René
 domicile : 65 boulevard Des Alpes 38240 Meylan - FRANCE

commissaire aux comptes suppléant

Monsieur NICOLAS Yves né(e) le 21 mars 1953 à LA VOULTE SUR RHONE (47) - France - de nationalité française
 Nom d'usage : Monsieur NICOLAS Yves
 domicile : 63 rue de Villiers 92208 Neuilly Sur Seine - FRANCE

dénomination

nom commercial

activité exercée

date de début d'activité

régime

mode d'exploitation

ETABLISSEMENT PRINCIPAL

Paris Technologique des Isolations chemin Des Franques 91190 Bernin - FRANCE

SOTIEC

L'activité exercée dans cet établissement est identique aux principales activités de l'entreprise

01 mars 1992

création

exploitation directe

MENTIONS ET OBSERVATIONS

Déposé 03 Mars 1992

IERS AFFICHES DE GRENOBLE DU 06 Mars 1992

mention effectuée le 29 septembre 1998

DECLARATION MODIFICATIVE du 29 Septembre 1998

Abandon de la RE SOTIEC FINANCE SA 398 277 871 RCS GRENOBLE à compter du 31.08.1998

mention effectuée le 06 septembre 2011 sous le N° F.11/010983

Changement de dénomination à compter du 24/06/2011 : Ancienne dénomination SOTIEC
 SIIJON ON INSULATOR TECHNOLOGIES

Toute modification ou falsification du présent extrait expose à des poursuites pénales
Seul le greffier est également habilité à délivrer des copies signées de l'original
toute reproduction du présent extrait même certifiée conforme est sans valeur

Pour extrait certifié conforme

DELIVRE à Grenoble le 06/09/2011

Le greffier



R. B. B.





April 23, 2012

Certification

Park IP Translations

This is to certify that the attached translation is, to the best of my knowledge and belief, a true and accurate translation from French into English of the document entitled "Extract from the Registry of Commerce and Companies" and with registration number "384 711 909 RCS Grenoble".

A handwritten signature in cursive script, reading 'Abraham I. Holczer', is written above a horizontal line.

Abraham I. Holczer

Project Manager

Park Case # 28762

134 W. 29th Street 5th Floor • New York, N.Y. 10001

Phone: 212-581-8870 • Fax: 212-581-5577

PATENT

REEL: 028138 FRAME: 0906

Extract from the Registry of Commerce and Companies

REGISTRATION AND IDENTITY OF THE LEGAL ENTITY

Registration Number: 384 711 909 RCS Grenoble
Date of Registration: March 11, 1992
Name: Soitec
Legal Structure: Corporation with a Board of Directors
Duration of the Legal Entity: 80 Years

CHARACTERISTICS OF THE ENTREPRISE

Capital: 12,210,579.20 EUROS
Corporate Headquarters: Parc Technologique des fontaines chemin des fontains 38190 Bernin - FRANCE
Principal Activities of the Enterprise: Research and Development, Manufacturing, Marketing of Materials for Microelectronics and for Industry in general, Diverse Technological Assistance, Development of Specific Machines and Applications. Ancillary manufacturing activity knowing that the main activity is research and development marketing.
Date of Closure of the Fiscal Year: March 31

DIRECTION, ADMINISTRATION, CONTROL

President of the Board of Directors: Mr. AUBERTON-HERVE, Andre, born on November 02, 1961 in RABAT – Morocco – of French nationality
Name of usage: Mr. AUBERTON-HERVE, Andre
Domicile: 12 ter chemin de Jaillieres 38240 Meylan – FRANCE

Director General: Mr. AUBERTON-HERVE, Andre, born on November 02, 1961 in RABAT – Morocco – of French nationality
Name of usage: Mr. AUBERTON-HERVE, Andre
Domicile: 12 ter chemin de Jaillieres 38240 Meylan – FRANCE

Representative of the General Director: Mr. BOUDRE, Paul Antoine, born on November 14, 1958 in TULLE (19) – France – of French nationality
Name of usage: Mr. BOUDRE, Paul
Domicile: 1492 route Cezanne 13100 le Tholonet – FRANCE

Administrator: Mr. HIROSE, Fumisato, born on July 06, 1947 in SAPPORO – Japan – of Japanese nationality
Name of usage: Mr. HIROSE, Fumisato
Domicile: 25 Northwood Park Deans Ligingston West Lothian eh 54 8 bd – GREAT BRITAIN

Administrator: Mr. MARTIN, Joseph Robert, born on December 09, 1947 in PENNSYLVANIA – United States of America – of American nationality
Name of usage: Mr. MARTIN, Joseph
Domicile: 17 Stornoway Road ME04110 Cumberland Foreside – UNITED STATES OF AMERICA

Administrator: Ms. GRANDCLEMENT, Annick Denise, born on May 24, 1956 in PARIS 16 District (75) – France – of French nationality
Name of usage: Ms. PASCAL, Annick
Domicile: 18 avenue Terre 95210 Saint-gratien - FRANCE

Office of the Clerk of the Commercial Court – place Firmin Gautier BP 150
38019 GRENOBLE Cedex 1
Tel: 04 56 58 50 50 – Fax: 04 56 58 50 00

**OFFICE OF THE CLERK OF THE COMMERCIAL COURT
GRENOBLE**

Administrative No.: **1992B00286**
Folio 2/3

09/06/2011 at 1:54 P.M.

Administrator: Mr. MURRAY, Patrick Foy, born on December 12, 1944 in MICHIGAN – United States of America – of American nationality
Name of usage: Mr. MURRAY, Patrick
Domicile: 40 avenue de Saxe 75007 Paris – FRANCE

Administrator: Mr. DUNN, Douglas John, born on May 05, 1944 in ROTHERHAM – Netherlands – of Dutch nationality
Name of usage: Mr. DUNN, Douglas
Domicile: Millstone Haouse Mill Lane Swindon sn 1 4hg – GREAT BRITAIN

Administrator: Mr. LAMOUCHE, Didier Rene, born on May 07, 1955 in MEKNES – Morocco – of French nationality
Name of usage: Mr. LAMOUCHE, Didier
Domicile: 6 rue du General Pershing 78000 Versailles – FRANCE

Regular Statutory Auditors: CABINET MURAZ PAVILLET Limited Liability Company - 349 333 690 RCS Grenoble Corporate Headquarters: 3 chemin du Vieux Chene 38240 Meylan – FRANCE

Regular Statutory Auditors: PRICEWATERHOUSECOOPERS AUDIT - 672 006 483 RCS Nanterre Corporate Headquarters: 63 rue de Villiers 92208 Neuilly Sur Seine – FRANCE

Alternate Statutory Auditors: Mr. PERROT, Rene Charles, born on June 22, 1948 in PONT DE BEAUVOISIN (38) – France – of French nationality
Name of usage: Mr. PERROT, Rene
Domicile: 65 boulevard des Alpes 38240 Meylan – FRANCE

Alternate Statutory Auditors: Mr. NICOLAS, Yves, born on March 21, 1955 in LA VOULTE SUR RHONE (07) – France – of French nationality
Name of usage: Mr. NICOLAS, Yves
Domicile: 63 rue de Villiers 92208 Neuilly Sur Seine – FRANCE

PRINCIPAL ESTABLISHMENT

Address: Fountains Technical Park des fontains Road 38190 Bernin – FRANCE

Commercial Name: SOITEC

Activity Carried Out: The activity carried out in this establishment is identical to the principal activities of the enterprise

Date Activity Began: March 01, 1992

Origin: Creation

Mode of Operation: Direct Operation

COMMENTS AND OBSERVATIONS

Filed on March 03, 1992

PUBLIC NOTICES OF GRENOBLE ON March 06, 1992

Notice made on September 29, 1998

-DECLARATION OF CHANGE of September 29, 1998:

Takeover of the company SOITEC FINANCE SA 398 277 871 RCS GRENOBLE beginning on 08/31/1998

Notice carried out on September 06, 2011 under No. FI 1/010983

-Name change beginning on 06/24/2011: Former name: S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES

Office of the Clerk of the Commercial Court – place Firmin Gautier BP 150
38019 GRENOBLE Cedex 1
Tel: 04 56 58 50 50 – Fax: 04 56 58 50 00

**PATENT
REEL: 028138 FRAME: 0908**

**OFFICE OF THE CLERK OF THE COMMERCIAL COURT
GRENOBLE**

Administrative No.: 1992B00286
09/06/2011 at 1:54 P.M.

Folio 3/3

*Any modification or falsification of this extract is subject to criminal prosecution.
Only the Court Clerk is legally empowered to issue original signed extracts.
any reproduction of this extract, even if notarized, is without value.*

By notarized extract,
ISSUED in Grenoble on 09/06/2011
The Court Clerk:-



[Handwritten signature]

Office of the Clerk of the Commercial Court – place Firmin Gautier BP 150
38019 GRENOBLE Cedex 1
Tel: 04 56 58 50 50 – Fax: 04 56 58 50 00

Attorney Docket No. 3356-001 (E11/0904 EHU)

Schedule A

	Application No.	Filing Date	Country	Attorney Docket No.	Title
1	12/310,345	2/20/2009	US	9373US (G04/0907BF EMT)	PROCESS FOR MAKING A GAN SUBSTRATE
2	12/463,873	5/11/2009	US	9451US (F07/0908BFA)	RELAXATION AND TRANSFER OF STRAINED LAYERS
3	12/450,295	9/18/2009	US	9629US (F06/0907 CF EBI)	A (110) ORIENTED SILICON SUBSTRATE AND A BONDED PAIR OF SUBSTRATES COMPRISING SAID (110) ORIENTED SILICON SUBSTRATE
4	12/563,327	9/21/2009	US	9200.1US (F07/1102CA)	METHODS AND STRUCTURES FOR ALTERING STRAIN IN III-NITRIDE MATERIALS
5	12/576,116	10/8/2009	US	8994.1US (F07/1101CA GLA)	METHODS OF FORMING LAYERS OF SEMICONDUCTOR MATERIAL HAVING REDUCED LATTICE STRAIN, SEMICONDUCTOR STRUCTURES, DEVICES AND ENGINEERED SUBSTRATES INCLUDING SAME
6	12/610,065	10/30/2009	US	8973.1US (F07/0902FL GLA)	STRAIN ENGINEERED COMPOSITE SEMICONDUCTOR SUBSTRATES AND METHODS OF FORMING SAME
7	12/610,092	10/30/2009	US	9358.1US (F08/1104CA GLA)	EPITAXIAL METHODS AND STRUCTURES FOR FORMING SEMICONDUCTOR MATERIALS
8	12/312,017	11/24/2009	US	9397US (F06/0604EN EBI)	IMPROVED PROCESS FOR TRANSFER OF A THIN LAYER FORMED IN A SUBSTRATE WITH VACANCY CLUSTERS

	Application No.	Filing Date	Country	Attorney Docket No.	Title
9	12/663,254	12/4/2009	US	9792US (F07/0110CAU EBI)	METHOD FOR RECYCLING A SUBSTRATE, LAMINATED WATER FABRICATING METHOD AND SUITABLE RECYCLED DONOR SUBSTRATE
10	12/598,403	2/25/2010	US	9703US (F06/1113KR EBI)	IMPROVED PROCESS FOR PREPARING CLEANED SURFACES OF STRAINED SILICON
11	12/712,938	2/25/2010	US	9928US (F08/1004SK EBI)	METHOD FOR TRANSFERRING A LAYER FROM A DONOR SUBSTRATE ONTO A HANDLE SUBSTRATE
12	12/726,800	3/18/2010	US	9944US (F08/0916BYN EBI)	HYBRID SEMICONDUCTOR SUBSTRATE INCLUDING SEMICONDUCTOR-ON-INSULATOR REGION AND METHOD OF MAKING THE SAME (As Amended)
13	12/742,424	5/11/2010	US	P10043US (F06/0806FA ALD)	PROCESS FOR MANUFACTURING A COMPOSITE SUBSTRATE
14	12/678,978	5/28/2010	US	9931US (F07/0502CA GLA)	SEMICONDUCTOR STRUCTURE HAVING A PROTECTIVE LAYER
15	12/814,936	6/14/2010	US	P10054US (F09/0204RB GLA)	SYSTEMS AND METHODS FOR A GAS TREATMENT OF A NUMBER OF SUBSTRATES
16	12/808,353	6/15/2010	US	P10041US (F06/1204AAB GLA)	METHOD FOR TREATING GERMANIUM SURFACES AND SOLUTIONS TO BE EMPLOYED THEREIN
17	12/820,326	6/22/2010	US	9588.1US (F09/0505CA GLA)	METHODS AND STRUCTURES FOR BONDING ELEMENTS

	Application No.	Filing Date	Country	Attorney Docket No.	Title
18	12/811,203	6/29/2010	US	P10034US (F07/0622CLN ALD)	PROCESS OF TREATING DEFECTS DURING THE BONDING OF WAFERS
19	12/837,326	7/15/2010	US	9975US (F10/0314 MSA GLA)	METHODS OF FORMING BONDED SEMICONDUCTOR STRUCTURES, AND SEMICONDUCTOR STRUCTURES FORMED BY SUCH METHODS
20	12/839,203	7/19/2010	US	9978US (F10/0313 MSA GLA)	TEMPORARY SEMICONDUCTOR STRUCTURE BONDING METHODS AND RELATED BONDED SEMICONDUCTOR STRUCTURES
21	12/865,838	8/2/2010	US	P10106US (F07/0509MSH ALD)	SUBSTRATE HAVING A CHARGED ZONE IN AN INSULATING BURIED LAYER
22	12/851,227	8/5/2010	US	P10123US (F07/0624CLN ALD)	PROCESS FOR BONDING AND TRANSFERRING A LAYER
23	12/879,637	9/10/2010	US	P10141US (F10/0502MSA GLA)	METHODS OF FORMING THROUGH WAFER INTERCONNECTS IN SEMICONDUCTOR STRUCTURES USING SACRIFICIAL MATERIAL, AND SEMICONDUCTOR STRUCTURES FORMED BY SUCH METHODS
24	12/890,220	9/24/2010	US	9583.2US (F09/0603 FLE)	METHODS OF FABRICATING SEMICONDUCTOR STRUCTURES AND DEVICES USING GLASS BONDING LAYERS, AND SEMICONDUCTOR STRUCTURES AND DEVICES FORMED BY SUCH METHODS

	Application No.	Filing Date	Country	Attorney Docket No.	Title
25	12/894,724	9/30/2010	US	P10058US (F100307RB GLA)	THERMALIZING GAS INJECTORS FOR GENERATING INCREASED PRECURSOR GAS, MATERIAL DEPOSITION SYSTEMS INCLUDING SUCH INJECTORS, AND RELATED METHODS
26	12/895,311	9/30/2010	US	P10096US (F10/0312CW GLA)	SYSTEMS AND METHODS FOR FORMING SEMICONDUCTOR MATERIALS BY ATOMIC LAYER DEPOSITION
27	12/935,857	9/30/2010	US	P10187US (F07/1106CA GLA)	FORMATION OF SUBSTANTIALLY PIT FREE INDIUM GALLIUM NITRIDE
28	12/936,639	11/15/2010	US	P10190US (F08/0613ACS ALD)	A METHOD OF INITIATING MOLECULAR BONDING
29	12/970,422	12/16/2010	US	P10171US (F10/0806MSA GLA)	METHODS FOR DIRECTLY BONDING TOGETHER SEMICONDUCTOR STRUCTURES, AND BONDED SEMICONDUCTOR STRUCTURES FORMED USING SUCH METHODS
30	12/977,999	12/23/2010	US	P10142US (F10/0419CW GLA)	STRAIN RELAXATION USING METAL MATERIALS AND RELATED STRUCTURES
31	13/020,288	2/3/2011	US	P10188US (F10/0901CW GLA)	METALLIC CARRIER FOR LAYER TRANSFER AND METHODS FOR FORMING THE SAME
32	13/029,213	2/17/2011	US	P10143US (F10/0503CFG GLA)	III-V SEMICONDUCTOR STRUCTURES WITH DIMINISHED PIT DEFECTS AND METHODS FOR FORMING THE SAME

	Application No.	Filing Date	Country	Attorney Docket No.	Title
33	13/060,398	2/23/2011	US	8900.1US (F08/0113CA GLA)	METHODS OF FABRICATING SEMICONDUCTOR STRUCTURES OR DEVICES USING LAYERS OF SEMICONDUCTOR MATERIAL HAVING SELECTED OR CONTROLLED LATTICE PARAMETERS
34	13/038,920	3/2/2011	US	P10345US (F10/0706CFG GLA)	METHODS OF FORMING III/V SEMICONDUCTOR MATERIALS, AND SEMICONDUCTOR STRUCTURES FORMED USING SUCH METHODS
35	13/043,088	3/8/2011	US	P10297US (F09/1010AV ALD)	PROCESS FOR FABRICATING A MULTILAYER STRUCTURE WITH POST-GRINDING TRIMMING
36	13/069,900	3/23/2011	US	9973.1US (F09/0902EL GLA)	III-V SEMICONDUCTOR STRUCTURES AND METHODS FOR FORMING THE SAME
37	13/077,292	3/31/2011	US	9979US (F10/0306 MSA GLA)	METHODS OF FORMING BONDED SEMICONDUCTOR STRUCTURES, AND SEMICONDUCTOR STRUCTURES FORMED BY SUCH METHODS
38	13/077,364	3/31/2011	US	P10010US (F10/0420MSA GLA)	METHODS OF FORMING BONDED SEMICONDUCTOR STRUCTURES INCLUDING TWO OR MORE PROCESSED SEMICONDUCTOR STRUCTURES CARRIED BY A COMMON SUBSTRATE, AND SEMICONDUCTOR STRUCTURES FORMED BY SUCH METHODS

	Application No.	Filing Date	Country	Attorney Docket No.	Title
39	13/076,745	3/31/2011	US	P10247US (F10/0902MSA GLA)	METHODS FOR BONDING SEMICONDUCTOR STRUCTURES INVOLVING ANNEALING PROCESSES, AND BONDED SEMICONDUCTOR STRUCTURES AND INTERMEDIATE STRUCTURES FORMED USING SUCH METHODS
40	12/937,920	4/5/2011	US	P10222US (F08/0507ND ALD)	PROCESS FOR MANUFACTURING A STRUCTURE COMPRISING A GERMANIUM LAYER ON A SUBSTRATE
41	13/123,180	4/7/2011	US	P10531US (F08/0608GWG ALD)	A METHOD OF PRODUCING A SILICON-ON-SAPPHIRE TYPE HETEROSTRUCTURE
42	13/126,376	4/27/2011	US	P10518US (F08/0717OK ALD)	METHOD TO FABRICATE AND TREAT A STRUCTURE OF SEMICONDUCTOR-ON-INSULATOR TYPE, ENABLING DISPLACEMENT OF DISLOCATIONS, AND CORRESPONDING STRUCTURE
43	13/133,118	6/8/2011	US	P10599US (F08/0115CLN ALD)	METHODS FOR TESTING SEMICONDUCTOR-ON-INSULATOR TYPE SUBSTRATES, AND SEMICONDUCTOR-ON-INSULATOR SUBSTRATES CONFIGURED FOR TESTING THEREOF
44	13/143,038	6/30/2011	US	P10639US (F08/0901DLN ALD)	A METHOD OF PRODUCING A LAYER OF CAVITIES
45	13/143,170	7/1/2011	US	P10658US (F08/0912GR ALD)	METHOD FOR MANUFACTURING COMPONENTS
46	13/185,044	7/18/2011	US	P10277US (F09/0406MSA GLA)	BONDING SURFACES FOR DIRECT BONDING OF SEMICONDUCTOR STRUCTURES
47	13/147,749	8/3/2011	US	P10682US (F08/0914PGU EMT)	ADAPTATION OF THE LATTICE PARAMETER OF A LAYER OF STRAINED

	Application No.	Filing Date	Country	Attorney Docket No.	Title
					MATERIAL
48	13/206,242	8/9/2011	US	P10284US (F10/1107BYN GLA)	METHODS OF FORMING BONDED SEMICONDUCTOR STRUCTURES INCLUDING INTERCONNECT LAYERS HAVING ONE OR MORE OF ELECTRICAL, OPTICAL, AND FLUIDIC INTERCONNECTS THEREIN, AND BONDED SEMICONDUCTOR STRUCTURES FORMED USING SUCH METHODS
49	13/206,280	8/9/2011	US	P10285US (F10/1106MSA GLA)	METHODS OF FORMING BONDED SEMICONDUCTOR STRUCTURES IN 3D INTEGRATION PROCESSES USING RECOVERABLE SUBSTRATES, AND BONDED SEMICONDUCTOR STRUCTURES FORMED BY SUCH METHODS
50	13/206,299	8/9/2011	US	P10424US (F10/1203BYN GLA)	THREE DIMENSIONALLY INTEGRATED SEMICONDUCTOR SYSTEMS INCLUDING PHOTOACTIVE DEVICES AND SEMICONDUCTOR-ON-INSULATOR SUBSTRATES, AND METHODS OF FORMING SUCH THREE DIMENSIONALLY INTEGRATED SEMICONDUCTOR SYSTEMS
51	13/201,365	8/12/2011	US	P10662US (F08/0724FLE EMT)	RELAXATION AND TRANSFER OF STRAINED MATERIAL LAYERS
52	13/255,670	10/18/2011	US	P10683US (F07/0801MRK ALD)	METHOD OF FABRICATING A MULTILAYER STRUCTURE WITH CIRCUIT LAYER TRANSFER